

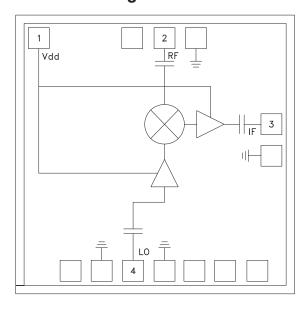
GaAs MMIC SUB-HARMONICALLY PUMPED DOWNCONVERTER, 20 - 32 GHz

Typical Applications

The HMC265 is ideal for:

- Microwave Point-to-Point Radios
- LMDS
- SATCOM

Functional Diagram



Features

Integrated LO Amplifier: -4 dBm Input Sub-Harmonically Pumped (x2) LO Integrated IF Amplifier: 3 dB Gain Small Size: 1.32 x 1.32 x 0.1 mm

General Description

The HMC265 chip is a sub-harmonically pumped (x2) MMIC downconverter with integrated LO & IF amplifiers. The chip utilizes a GaAs PHEMT technology that results in a small overall chip area of 1.74 mm². The 2LO to RF isolation is excellent eliminating the need for additional filtering. The LO amplifier is a single bias (+3V to +4V) two stage design with only -4 dBm nominal drive requirement. All data is with the chip in a 50 ohm test fixture connected via 0.025 mm (1 mil) diameter wire bonds of minimal length <0.31 mm (<12 mils). This downconverter IC is an excellent, smaller, and more reliable replacement to hybrid diode based downconverter MMIC assemblies.

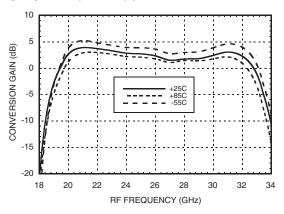
Electrical Specifications, $T_A = +25^{\circ}$ C, LO Drive = -4 dBm

Parameter	IF = 1 GHz Vdd = +4V			IF = 1 GHz Vdd = +4V			Units
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Frequency Range, RF	20 - 32			27 - 30			GHz
Frequency Range, LO	10 - 16				13.5 - 15		GHz
Frequency Range, IF	0.7 - 3.0		0.7 - 3.0		GHz		
Conversion Gain (RF to IF)	-2	3	7	-2	2	5	dB
Noise Figure (SSB)		13			13		dB
2LO to RF Isolation	17	20 ~ 40		28	35		dB
2LO to IF Isolation	40	50 ~ 60		45	55		dB
IP3 (Input)	2	10		9	13		dBm
1 dB Compression (Input)	-5	2		-2	2		dBm
Supply Current (Idd)		50	67		50	67	mA

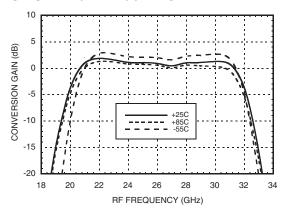


GaAs MMIC SUB-HARMONICALLY PUMPED DOWNCONVERTER, 20 - 32 GHz

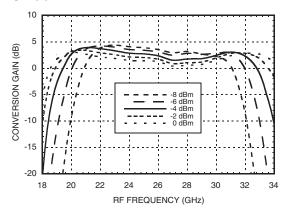
Conversion Gain vs. Temperature @ LO = -4 dBm Vdd = +4V



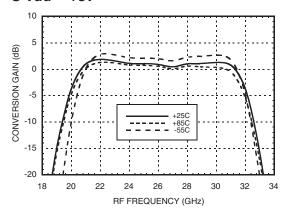
Conversion Gain vs. Temperature @ LO = -4 dBm Vdd = +3V



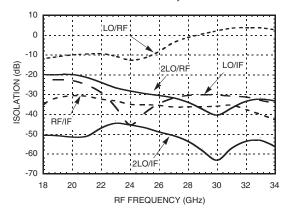
Conversion Gain vs. LO Drive @ Vdd = +4V



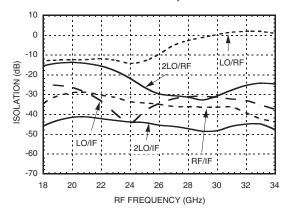
Conversion Gain vs. LO Drive @ Vdd = +3V



Isolation @ LO = -4 dBm, Vdd = +4V



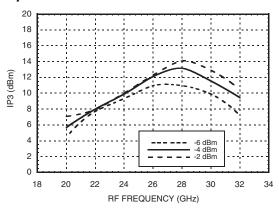
Isolation @ LO = -4 dBm, Vdd = +3V



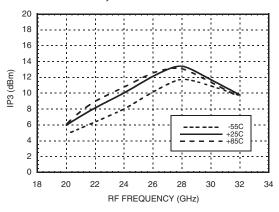


GaAs MMIC SUB-HARMONICALLY PUMPED DOWNCONVERTER, 20 - 32 GHz

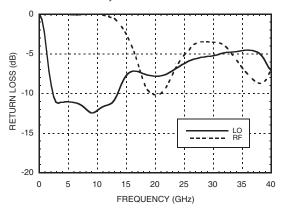
Input P3 vs. LO Drive @ Vdd = +4V



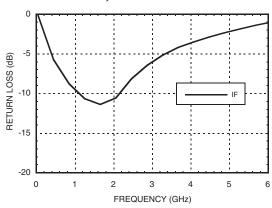
Input P3 vs. Temperature @LO = -4 dBm, Vdd = +4V



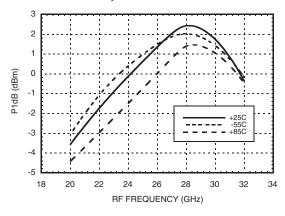
LO & RF Return Loss @ LO = -4 dBm, Vdd = +4V



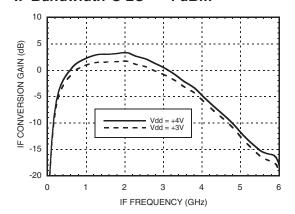
IF Return Loss @ LO = -4 dBm, Vdd = +4V



Input P1dB vs. Temperature @ LO = -4 dBm, Vdd = +4V



IF Bandwidth @ LO = -4 dBm





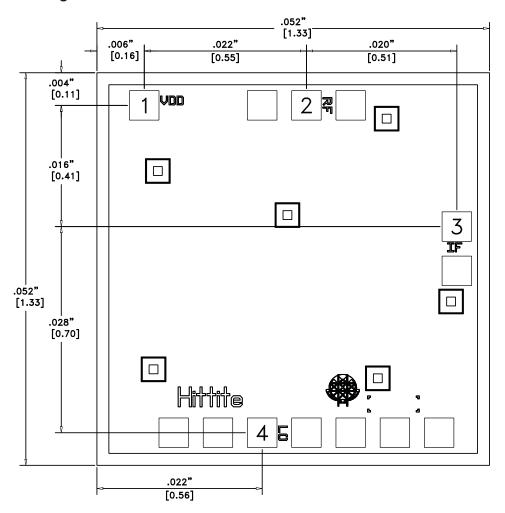
GaAs MMIC SUB-HARMONICALLY PUMPED DOWNCONVERTER, 20 - 32 GHz

Absolute Maximum Ratings

RF / IF Input (Vdd = +4V)	+13 dBm	
LO Drive (Vdd = +4V)	+13 dBm	
Vdd	+5.5 Vdc	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-55 to +85 °C	



Outline Drawing



Die Packaging Information [1]

Standard	Alternate	
GP-2 (Gel Pack)	[2]	

- [1] Refer to the "Packaging Information" section for die packaging dimensions.
- [2] For alternate packaging information contact Hittite Microwave Corporation.

NOTES:

- 1. ALL DIMENSIONS ARE IN INCHES [MM].
- 2. DIE THICKNESS IS .004".
- 3. TYPICAL BOND PAD IS .004" SQUARE.
- 4. BOND PAD SPACING CENTER TO CENTER IS .006".
- 5. BACKSIDE METALLIZATION: GOLD.
- 6. BOND PAD METALLIZATION: GOLD.
- 7. BACKSIDE METAL IS GROUND.
- 8. CONNECTION NOT REQUIRED FOR UNLABELED BOND PADS.



GaAs MMIC SUB-HARMONICALLY PUMPED DOWNCONVERTER, 20 - 32 GHz

Pad Descriptions

Pad Number	Function	Description	Interface Schematic
1	Vdd	Power supply for the LO Amplifier. An external RF bypass capacitor of 100 - 330 pF is required. A MIM border capacitor is recommended. The bond length to the capacitor should be as short as possible. The ground side of the capacitor should be connected to the housing ground.	Vdd ———————————————————————————————————
2	RF	This pad is AC coupled and matched to 50 Ohm.	RF 0
3	IF	This pad is AC coupled and matched to 50 Ohm.	
4	LO	This pad is AC coupled and matched to 50 Ohm.	L0 0──────



GaAs MMIC SUB-HARMONICALLY PUMPED DOWNCONVERTER, 20 - 32 GHz

Mounting & Bonding Techniques for Millimeterwave GaAs MMICs

The die should be attached directly to the ground plane eutectically or with conductive epoxy (see HMC general Handling, Mounting, Bonding Note).

50 Ohm Microstrip transmission lines on 0.127mm (5 mil) thick alumina thin film substrates are recommended for bringing RF to and from the chip (Figure 1). If 0.254mm (10 mil) thick alumina thin film substrates must be used, the die should be raised 0.150mm (6 mils) so that the surface of the die is coplanar with the surface of the substrate. One way to accomplish this is to attach the 0.102mm (4 mil) thick die to a 0.150mm (6 mil) thick molybdenum heat spreader (moly-tab) which is then attached to the ground plane (Figure 2).

Microstrip substrates should be brought as close to the die as possible in order to minimize bond wire length. Typical die-to-substrate spacing is 0.076mm (3 mils).

An RF bypass capacitor should be used on the Vdd input. A 100 pF single layer capacitor (mounted eutuctically or by conductive epoxy) placed no further than 0.762mm (30 Mils) from the chip is recommended. The photo in figure 3 shows a typical assembly for the HMC265 MMIC chip.

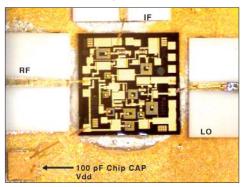


Figure 3: Typical HMC265 Assembly

Handling Precautions

Follow these precautions to avoid permanent damage.

Storage: All bare die are placed in either Waffle or Gel based ESD protective containers, and then sealed in an ESD protective bag for shipment. Once the sealed ESD protective bag has been opened, all die should be stored in a dry nitrogen environment.

Cleanliness: Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems. Static Sensitivity: Follow ESD precautions to protect against ESD strikes.

Transients: Suppress instrument and bias supply transients while bias is applied. Use shielded signal and bias cables to minimize inductive pick-up.

General Handling: Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers. The surface of the chip has fragile air bridges and should not be touched with vacuum collet, tweezers, or fingers.

Mounting

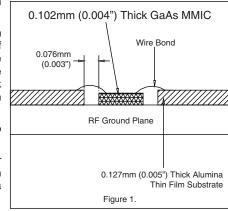
The chip is back-metallized and can be die mounted with AuSn eutectic preforms or with electrically conductive epoxy. The mounting surface should be clean and flat.

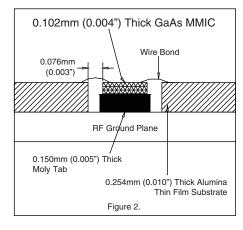
Eutectic Die Attach: A 80/20 gold tin preform is recommended with a work surface temperature of 255 °C and a tool temperature of 265 °C. When hot 90/10 nitrogen/hydrogen gas is applied, tool tip temperature should be 290 °C. DO NOT expose the chip to a temperature greater than 320 °C for more than 20 seconds. No more than 3 seconds of scrubbing should be required for attachment.

Epoxy Die Attach: Apply a minimum amount of epoxy to the mounting surface so that a thin epoxy fillet is observed around the perimeter of the chip once it is placed into position. Cure epoxy per the manufacturer's schedule.

Wire Bonding

Ball or wedge bond with 0.025 mm (1 mil) diameter pure gold wire. Thermosonic wirebonding with a nominal stage temperature of 150 °C and a ball bonding force of 40 to 50 grams or wedge bonding force of 18 to 22 grams is recommended. Use the minimum level of ultrasonic energy to achieve reliable wirebonds. Wirebonds should be started on the chip and terminated on the package or substrate. All bonds should be as short as possible <0.31 mm (12 mils).





X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for RF Mixer category:

Click to view products by Analog Devices manufacturer:

Other Similar products are found below:

HMC337-SX HMC404-SX mamx-009646-23dbml HMC339-SX HMC8192-SX MIQ24MS-2 HMC220BMS8GETR M85C HMC554A-SX HMC8192LG HMC521A-SX HMC521A-CHIPS CMD258C4 LT5511EFE MAMX-011023-SMB HMC399MS8TR HMC333TR HMC214MS8TR HMC175MS8TR MAMXSS0012TR-3000 109728-HMC129LC4 CSM1-13 SA612AD/01.112 HMC785LP4ETR LT5526EUF#PBF LT5579IUH#PBF HMC773ALC3BTR HMC558ALC3B HMC329ALC3B MY63H AD8343ARUZ-REEL7 AD608AR AD608ARZ AD831APZ AD831APZ-REEL7 AD8342ACPZ-REEL7 AD8343ARUZ AD8344ACPZ-REEL7 ADL5350ACPZ-R7 ADL5365ACPZ-R7 ADL5801ACPZ-R7 ADL5802ACPZ-R7 HMC1056LP4BE HMC1057-SX HMC1063LP3E HMC1093-SX HMC1106-SX HMC129 HMC143